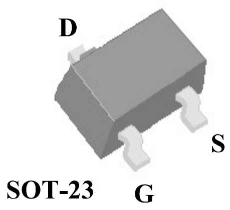
AP2N7002

N-Channel Power MOSFET

- ▼ **Simple Drive Requirement**
- ▼ **Small Package Outline**
- ▼ **Surface Mount Device**
- ▼ **RoHS Compliant & Halogen-Free**

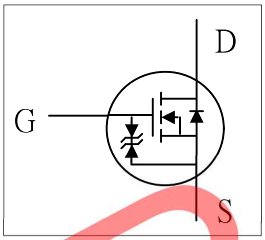


BV_{DSS}	60V
$R_{DS(ON)}$	2Ω
I_D	450mA

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-23 package is universally used for all commercial-industrial applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current[3], V_{GS} @ 10V	450	mA
I_D@T_A=70℃	Continuous Drain Current[3], V_{GS} @ 10V	360	mA
I_{DM}	Pulsed Drain Current[1]	950	mA
P_D@T_A=25℃	Total Power Dissipation	0.7	W
	Linear Derating Factor	0.005	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	180	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	60	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=1mA	-	0.06	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=450mA	-	-	2	Ω
		V_{GS}=4.5V, I_D=200mA	-	-	4	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	2.5	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=450mA	-	400	-	mS
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V, V_{GS}=0V	-	-	10	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=48V ,V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±30	uA
Q_g	Total Gate Charge[2]	I_D=450mA	-	1	1.6	nC
Q_{gs}	Gate-Source Charge	V_{DS}=50V	-	0.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	0.5	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=30V	-	12	-	ns
t_r	Rise Time	I_D=450mA	-	10	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=10V	-	56	-	ns
t_f	Fall Time	R_D=52Ω	-	29	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	32	50	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	8	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	6	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=450mA, V_{GS}=0V	-	-	1.2	V

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board t≦10sec; 400℃/W when mounted on min. copper pad.

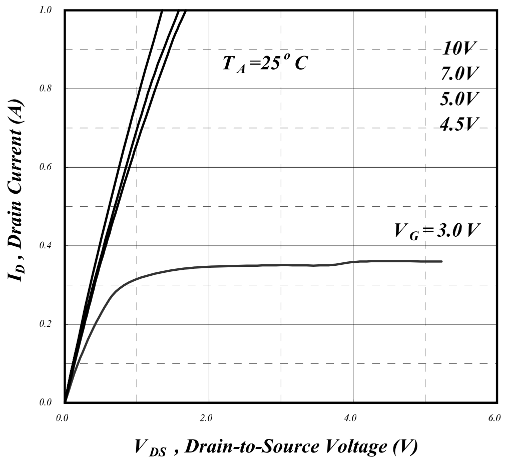


Fig 1. Typical Output Characteristics

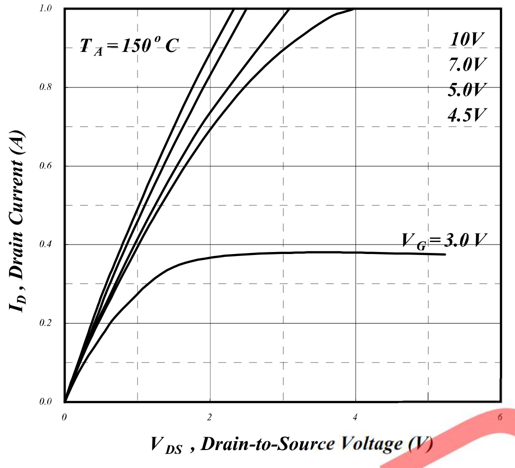


Fig 2. Typical Output Characteristics

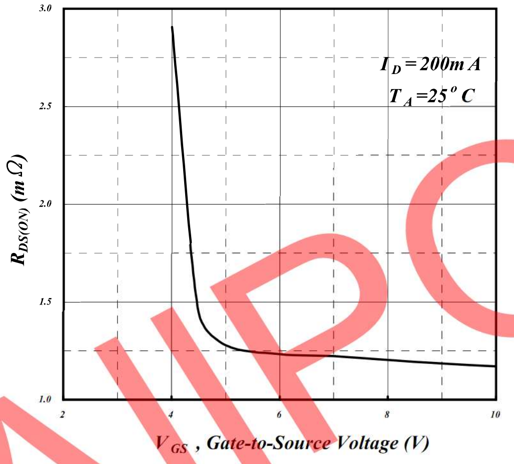


Fig 3. On-Resistance v.s. Gate Voltage

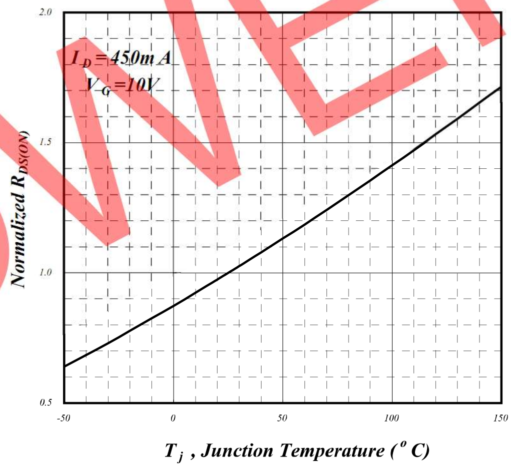


Fig 4. Normalized On-Resistance v.s. Junction Temperature

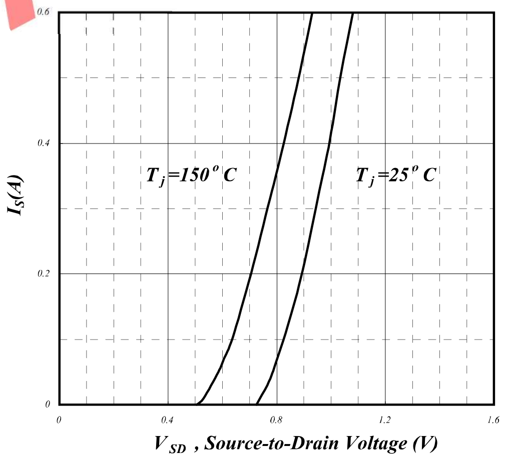


Fig 5. Forward Characteristic of Reverse Diode

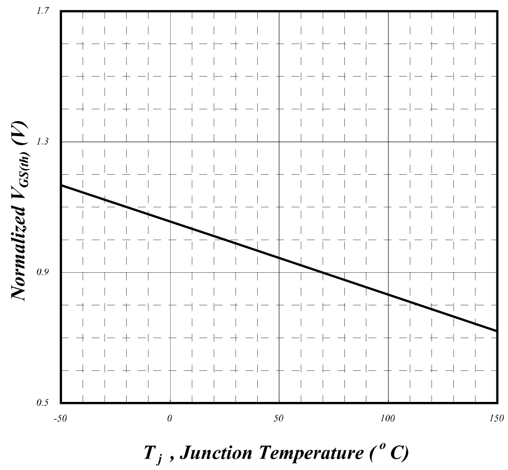


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

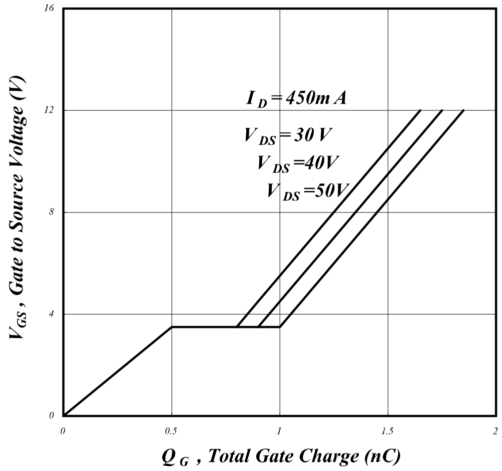


Fig 7. Gate Charge Characteristics

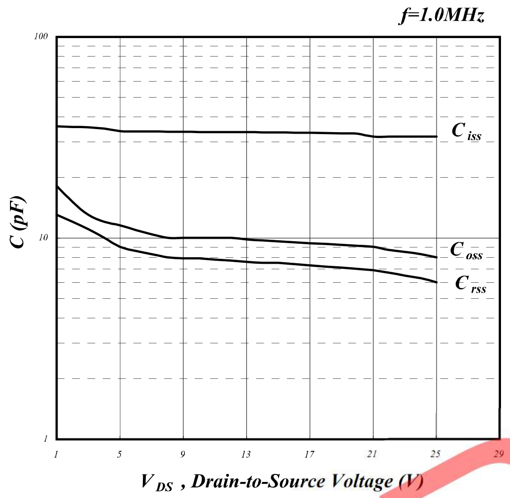


Fig 8. Typical Capacitance Characteristics

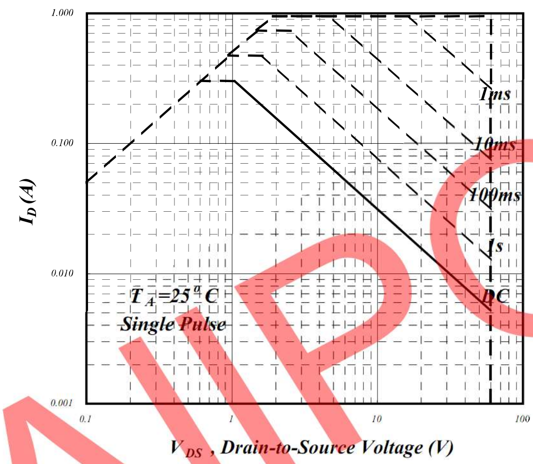


Fig 9. Maximum Safe Operating Area

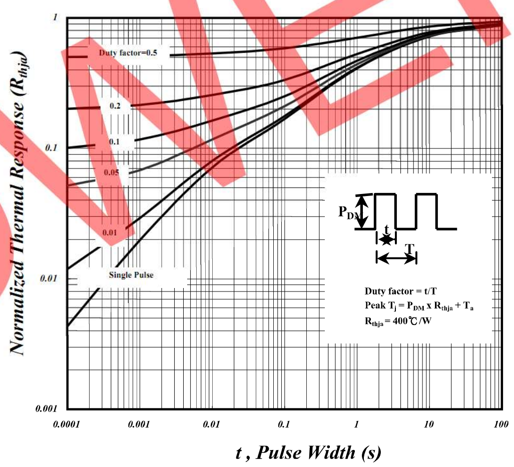


Fig 10. Effective Transient Thermal Impedance

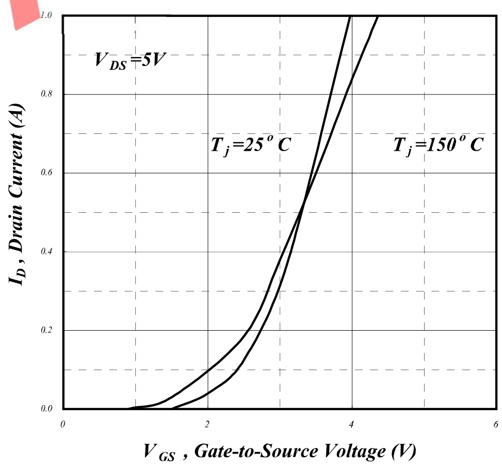


Fig 11. Transfer Characteristics

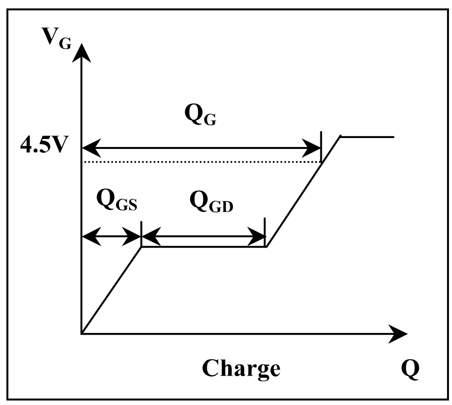


Fig 12. Gate Charge Waveform